

Silicon PNP Power Transistors

2N6049

DESCRIPTION

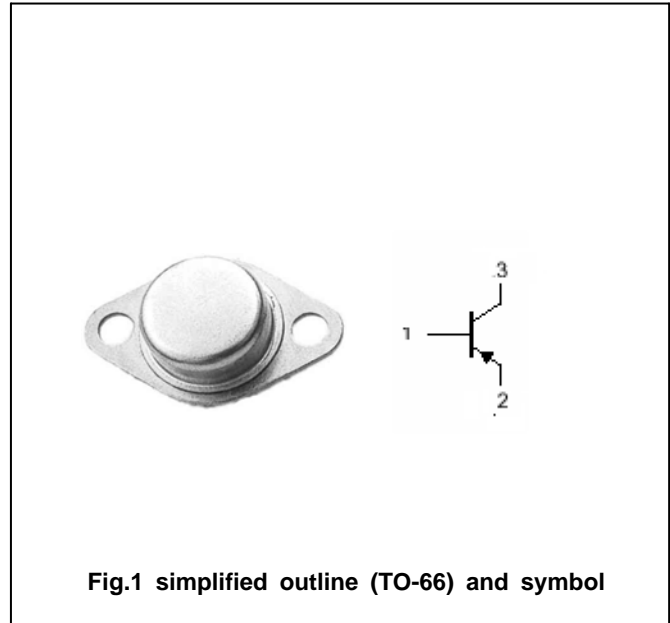
- With TO-66 package
- Complement to type 2N3054A

APPLICATIONS

- Designed for general purpose switching and amplifier applications

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-90	V
V_{CEO}	Collector-emitter voltage	Open base	-55	V
V_{EBO}	Emitter-base voltage	Open collector	-7	V
I_C	Collector current		-4	A
I_{CM}	Collector current-peak		-10	A
I_B	Base current		-2	A
P_D	Power dissipation	$T_C=25^\circ\text{C}$	75	W
T_j	Junction temperature		200	$^\circ\text{C}$
T_{stg}	Storage temperature		-65~200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	2.33	$^\circ\text{C}/\text{W}$

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CHARACTERISTICS

 $T_j=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C=-0.1A$; $I_B=0$	-55			V
$V_{CEsat-1}$	Collector-emitter saturation voltage	$I_C=-0.5A$; $I_B=-50mA$			-0.5	V
$V_{CEsat-2}$	Collector-emitter saturation voltage	$I_C=-4A$; $I_B=-0.8A$			-2.0	V
V_{BE}	Base -emitter on voltage	$I_C=-0.5A$; $V_{CE}=-4V$			-1.0	V
I_{CEX}	Collector cut-off current	$V_{CE}=-90V$; $V_{BE(off)}=-1.5V$ $T_C=150^\circ\text{C}$			-1.0 -6.0	mA
I_{CEO}	Collector cut-off current	$V_{CE}=-30V$; $I_B=0$			-0.5	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=-7V$; $I_C=0$			-1.0	mA
h_{FE-1}	DC current gain	$I_C=-0.5A$; $V_{CE}=-4V$	25		100	
h_{FE-2}	DC current gain	$I_C=-3A$; $V_{CE}=-4V$	6			
C_{OB}	Output capacitance	$I_E=0$; $V_{CB}=-10V$; $f=0.1MHz$			200	pF
f_T	Transition frequency	$I_C=-0.2A$; $V_{CE}=-10V$; $f=1MHz$	3.0			

PACKAGE OUTLINE

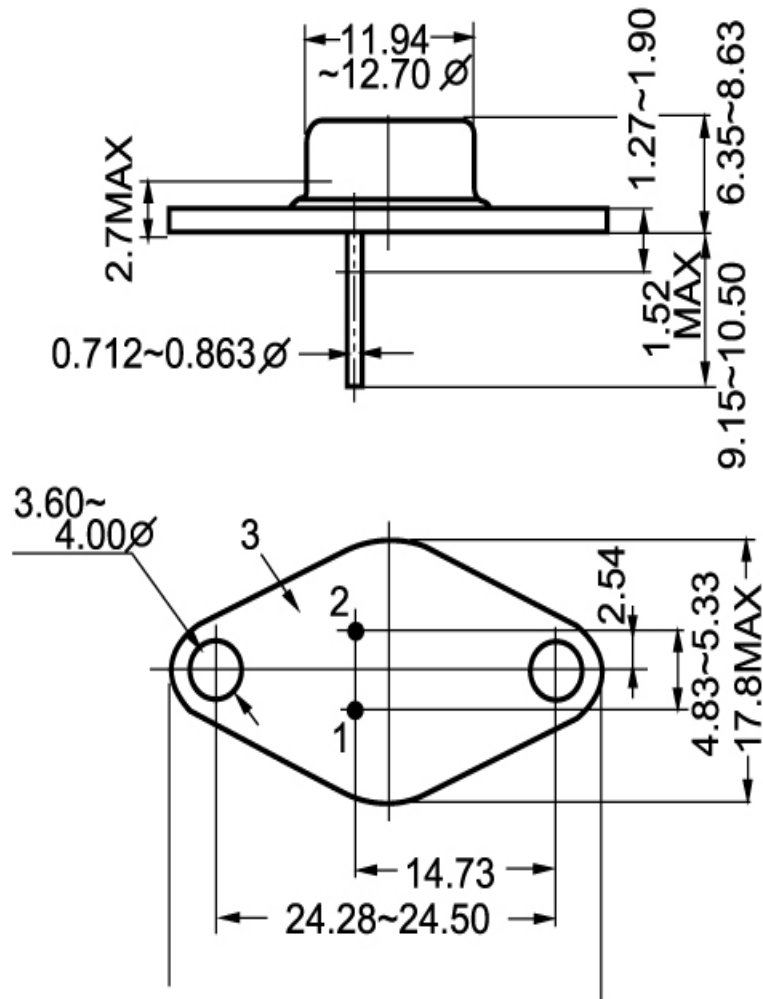


Fig.2 Outline dimensions